

# **Complementary Silicon Plastic Power Transistors**

Specifically designed for power audio output, or high power drivers in audio amplifiers.

- DC Current Gain Specified up to 8.0 Amperes at Temperature
- All On Characteristics at Temperature
- High SOA: 20 A, 18 V, 100 ms
- TO-247AE Package

# **MAXIMUM RATINGS**

| Rating   | Symbol                            | MJW21191<br>MJW21192 | Unit          |
|--|-----------------------------------|----------------------|---------------|
| Collector–Emitter Voltage  | V <sub>CEO</sub>                  | 150                  | Vdc           |
| Collector-Base Voltage   | $V_{CB}$                          | 150                  | Vdc           |
| Emitter–Base Voltage   | V <sub>EB</sub>                   | 5.0                  | Vdc           |
| Collector Current — Continuous<br>— Peak                             | IC                                | 8.0<br>16            | Adc           |
| Base Current   | I <sub>B</sub>                    | 2.0                  | Adc           |
| Total Power Dissipation @ T <sub>C</sub> = 25°C<br>Derate above 25°C | P <sub>D</sub>                    | 125<br>0.65          | Watts<br>W/°C |
| Operating and Storage Junction<br>Temperature Range                  | T <sub>J</sub> , T <sub>stg</sub> | -65 to +150          | °C            |

# THERMAL CHARACTERISTICS

| Characteristic                          | Symbol          | Max | Unit |
|---|-----------------|-----|------|
| Thermal Resistance, Junction to Case    | $R_{\theta JC}$ | 1.0 | °C/W |
| Thermal Resistance, Junction to Ambient | $R_{\theta JA}$ | 50  | °C/W |

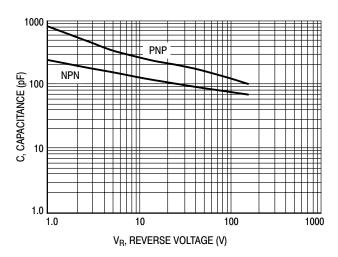
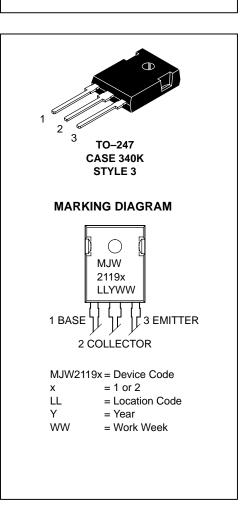


Figure 1. Typical Capacitance @ 25°C

# NPN MJW21192 PNP MJW21191

8.0 AMPERES
POWER TRANSISTORS
COMPLEMENTARY SILICON
150 VOLTS
125 WATTS



# **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

| Characteristic  | Symbol                | Min       | Max        | Unit |
|---|-----------------------|-----------|------------|------|
| OFF CHARACTERISTICS   | •                     | •         | •          | •    |
| Collector–Emitter Sustaining Voltage (1) $(I_C = 10 \text{ mAdc}, I_B = 0)$   | V <sub>CEO(sus)</sub> | 150       | _          | Vdc  |
| Collector Cutoff Current<br>(V <sub>CB</sub> = 250 Vdc, I <sub>E</sub> = 0)   | I <sub>CES</sub>      | _         | 10         | μAdc |
| Emitter Cutoff Current<br>(V <sub>BE</sub> = 5.0 Vdc, I <sub>C</sub> = 0)   | I <sub>EBO</sub>      | _         | 10         | μAdc |
| ON CHARACTERISTICS (1)  |                       |           |            |      |
| DC Current Gain $(I_C = 4.0 \text{ Adc}, V_{CE} = 2.0 \text{ Vdc})$ $(I_C = 8.0 \text{ Adc}, V_{CE} = 2.0 \text{ Vdc})$   | h <sub>FE</sub>       | 15<br>5.0 | _          | 100  |
| Collector–Emitter Saturation Voltage ( $I_C = 4.0$ Adc, $I_B = 0.4$ Adc) ( $I_C = 8.0$ Adc, $I_B = 1.6$ Adc)              | V <sub>CE(sat)</sub>  | _         | 1.0<br>2.0 | Vdc  |
| Base–Emitter On Voltage<br>(I <sub>C</sub> = 4.0 Adc, V <sub>CE</sub> = 2.0 Vdc)  | V <sub>BE(on)</sub>   | _         | 2.0        | Vdc  |
| DYNAMIC CHARACTERISTICS   | •                     | •         | •          | •    |
| Current Gain — Bandwidth Product (2)<br>(I <sub>C</sub> = 1.0 Adc, V <sub>CE</sub> = 10 Vdc, f <sub>test</sub> = 1.0 MHz) | f <sub>T</sub>        | 4.0       | _          | MHz  |

<sup>(1)</sup> Pulse Test: Pulse Width  $\leq 300 \,\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

<sup>(2)</sup>  $f_T = |h_{fe}| \cdot f_{test}$ 

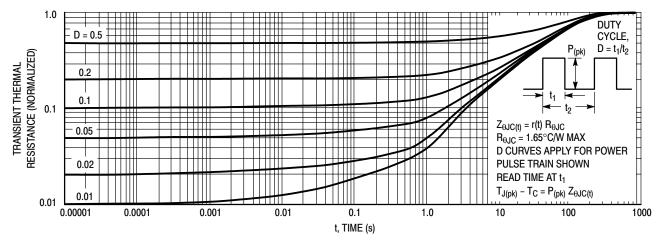


Figure 2. Thermal Response

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation then the curves indicate.

The data of Figures 3 and 4 is based on  $T_{J(pk)} = 150$  °C;  $T_C$  is variable depending on conditions. Second breakdown

pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)}$  < 150°C.  $T_{J(pk)}$  may be calculated from the data in Figure 2. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

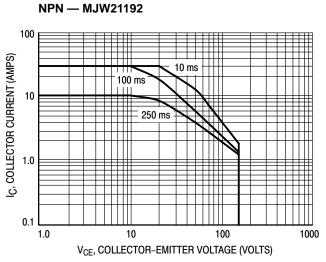


Figure 3. NPN — MJW21192 Safe Operating Area

# PNP — MJW21191

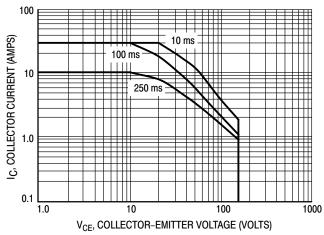
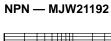


Figure 4. PNP — MJW21191 Safe Operating Area

# **TYPICAL CHARACTERISTICS**



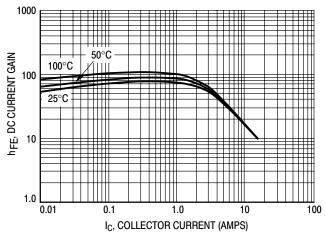


Figure 5. NPN — MJW21192 V<sub>CE</sub> = 2.0 V DC Current Gain

# PNP — MJW21191

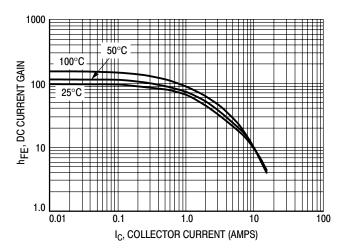


Figure 6. PNP — MJW21191 V<sub>CE</sub> = 2.0 V DC Current Gain

# NPN — MJW21192 1000 50°C h<sub>FE</sub>, DC CURRENT GAIN 100°C 100 0.01 0.1 1.0 100 I<sub>C</sub>, COLLECTOR CURRENT (AMPS) Figure 7. NPN — MJW21192 V<sub>CE</sub> = 5.0 V DC Current Gain

# PNP — MJW21191

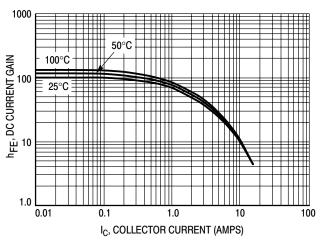
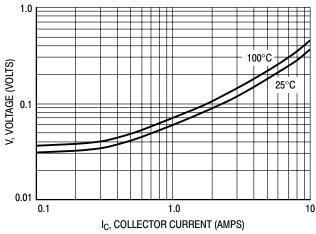


Figure 8. PNP — MJW21191 V<sub>CE</sub> = 5.0 V DC Current Gain



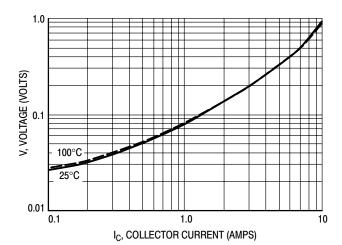
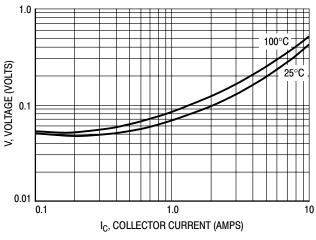


Figure 9. NPN — MJW21192  $V_{CE(sat)} I_C/I_B = 5.0$ 

Figure 10. PNP — MJW21191  $V_{CE(sat)} I_C/I_B = 5.0$ 



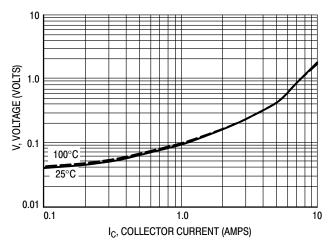


Figure 11. NPN — MJW21192  $V_{CE(sat)} I_C/I_B = 10$ 

Figure 12. PNP — MJW21191  $V_{CE(sat)} I_C/I_B = 10$ 

# NPN — MJW21192

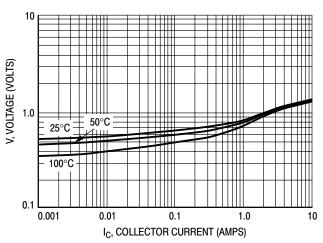


Figure 13. NPN — MJW21192  $V_{CE} = 2.0 \text{ V } V_{BE(on)} \text{ Curve}$ 

# PNP — MJW21191

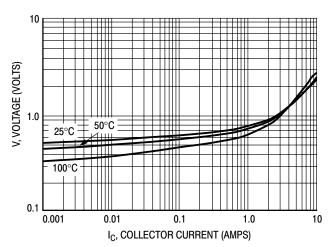


Figure 14. PNP — MJW21191  $V_{CE} = 2.0 \text{ V } V_{BE(on)} \text{ Curve}$ 





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